

CONTENTS

Preface	v
Simulation and Experimental Results on GaN Based Ultra-Short Planar Negative Differential Conductivity Diodes for THz Power Generation <i>B. Aslan, L. F. Eastman and Q. Diduck</i>	1
5-Terminal THz GaN Based Transistor with Field- and Space-Charge Control Electrodes <i>G. Simin, M. S. Shur and R. Gaska</i>	7
Performance Comparison of Scaled III-V and Si Ballistic Nanowire MOSFETs <i>L. Wang, B. Yu, P. M. Asbeck, Y. Taur and M. Rodwell</i>	15
A Room Temperature Ballistic Deflection Transistor for High Performance Applications <i>Q. Diduck, H. Irie and M. Margala</i>	23
Emission and Intensity Modulation of Terahertz Electromagnetic Radiation Utilizing 2-Dimensional Plasmons in Dual-Grating-Gate HEMT's <i>T. Otsuji, T. Nishimura, Y. Tsuda, Y. M. Meziani, T. Suemitsu and E. Sano</i>	33
Millimeter Wave to Terahertz in CMOS <i>K. K. O, S. Sankaran, C. Cao, E.-Y. Seok, D. Shim, C. Mao and R. Han</i>	55
The Effects of Increasing AlN Mole Fraction on the Performance of AlGaN Active Regions Containing Nanometer Scale Compositionally Inhomogeneities <i>A. V. Sampath, M. L. Reed, C. Moe, G. A. Garrett, E. D. Readinger, W. L. Sarney, H. Shen, M. Wraback, C. Chua and N. M. Johnson</i>	69
Surface Acoustic Wave Propagation in GaN-On-Sapphire Under Pulsed Sub-Band Ultraviolet Illumination <i>V. S. Chivukula, D. Ciplys, K. Liu, M. S. Shur and R. Gaska</i>	77
Solar-Blind Single-Photon 4H-SiC Avalanche Photodiodes <i>A. Vert, S. Soloviev, J. Fronheiser and P. Sandvik</i>	85
Monte Carlo Simulations of In _{0.75} Ga _{0.25} As MOSFETs at 0.5 V Supply Voltage for High-Performance CMOS <i>J. S. Ayubi-Moak, K. Kalna and A. Asenov</i>	93

The First 70nm 6-Inch GaAs PHEMT MMIC Process	101
<i>H. Karimy, L. Gunter, D. Dugas, P. C. Chao, W. Kong, S. Yang, P. Seekell, K. H. G. Duh, J. Lombardi and L. Mt Pleasant</i>	
High-Performance 50-nm Metamorphic High Electron-Mobility Transistors with High Breakdown Voltages	107
<i>D. Xu, W. M. T. Kong, X. Yang, P. Seekell, L. Mohnkern, H. Karimy, K. H. G. Duh, P. M. Smith and P. C. Chao</i>	
MBE Growth and Characterization of Mg-Doped III-Nitrides on Sapphire	113
<i>X. Chen, K. D. Matthews, D. Hao, W. J. Schaff, L. F. Eastman, W. Walukiewicz, J. W. Ager and K. M. Yu</i>	
Performance of MOSFETs on Reactive-Ion-Etched GaN Surfaces	121
<i>K. Tang, W. Huang, T. P. Chow</i>	
High Current Density/High Voltage AlGaIn/GaN HFETs on Sapphire	129
<i>J. Shi, M. Pophristic and L. F. Eastman</i>	
InAlN/GaN MOS-HEMT with Thermally Grown Oxide	137
<i>M. Alomari, F. Medjdoub, E. Kohn, M-A. di Forte-Poisson, S. Delage, J.-F. Carlin, N. Grandjean and C. Gaquière</i>	
GaN Transistors for Power Switching and Millimeter-Wave Applications	145
<i>T. Ueda, Y. Uemoto, T. Tanaka and D. Ueda</i>	
4-nm AlN Barrier All Binary HFET with SiN _x Gate Dielectric	153
<i>T. Zimmermann, Y. Cao, D. Jena, H. G. Xing and P. Saunier</i>	
Effect of Gate Oxide Processes on 4H-SiC MOSFETs on (000-1) Oriented Substrate	161
<i>H. Naik, K. Tang and T. P. Chow</i>	
Characterization and Modeling of Integrated Diode in 1.2kV 4H-SiC Vertical Power MOSFET	167
<i>H. Naik, Y. Wang and T. P. Chow</i>	
Packaging and Wide-Pulse Switching of 4 mm x 4 mm Silicon Carbide GTOs	173
<i>H. O'Brien and M. G. Koebke</i>	
Bi-Directional Scalable Solid-State Circuit Breakers for Hybrid-Electric Vehicles	183
<i>D. P. Urciuoli and V. Veliadis</i>	